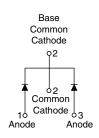


HALOGEN

FREE

Hyperfast Rectifier, 30 A FRED Pt®





PRIMARY CHARACTERISTICS					
D ² PAK (TO-263AB)					
2 x 15 A					
200 V					
0.78 V					
30 ns					
175 °C					
Common cathode					

FEATURES

- · Hyperfast recovery time
- Low forward voltage drop
- Low leakage current
- 175 °C operating junction temperature
- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C
- · AEC-Q101 qualified, class 1 whisker test
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

Vishay Semiconductors 200 V series are the state of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control, guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diode in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS							
PARAMETER		SYMBOL	TEST CONDITIONS	MAX.	UNITS		
Peak repetitive reverse voltage		V_{RRM}		200	V		
Average rectified forward current	per diode	1	T _C = 159 °C	15			
	per device	I _{F(AV)}		30	Α		
Non-repetitive peak surge current		I _{FSM}	T _C = 25 °C	200			
Operating junction and storage temperatures		T _J , T _{Stg}		-55 to +175	°C		

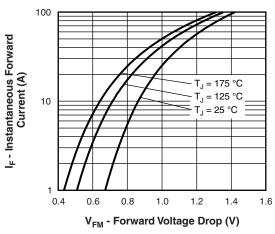
ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Breakdown voltage, blocking voltage	V_{BR}, V_{R}	Ι _R = 100 μΑ	200	-	-	V	
Forward voltage	V _E	I _F = 15 A	-	0.92	1.05	V	
Forward voltage	V _F	I _F = 15 A, T _J = 125 °C	-	0.78	0.85	V	
Poverse leekage ourrent		$V_R = V_R$ rated	-	-	10		
Reverse leakage current	I _R	$T_J = 125 ^{\circ}C$, $V_R = V_R$ rated	-	5	300	μΑ	
Junction capacitance	C _T	V _R = 200 V	-	57	-	pF	
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8	-	nH	

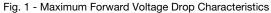




DYNAMIC RECOVERY CHARACTERISTICS (T _C = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS	
		$I_F = 1 A, dI_F/dt = 1$	00 A/μs, V _R = 30 V	-	-	30	
Reverse recovery time	t _{rr}	T _J = 25 °C	I _F = 15 A dI _F /dt = 200 A/μs V _R = 160 V	-	26	-	ns - A
		T _J = 125 °C		-	40	-	
Dools woodstant outwort	I _{RRM}	T _J = 25 °C		-	2.8	-	
Peak recovery current		T _J = 125 °C		-	6.0	-	
Reverse recovery charge	Q _{rr}	T _J = 25 °C		-	37	-	nC
		T _J = 125 °C		-	120	=	i iiC

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNITS		
Maximum junction and storage temperature range	T _J , T _{Stg}	-55	-	175	°C		
Thermal resistance, junction to case per diode	R_{thJC}	-	-	1.1	°C/W		
Wester		-	2.0	-	g		
Weight		-	0.07	-	OZ.		
Mounting torque		6.0	_	12	kgf · cm		
Wodning torque		(5.0)		(10)	(lbf · in)		
Marking device		Case style D ² PAK (TO-263AB) 30CTH02SH			H02SH		





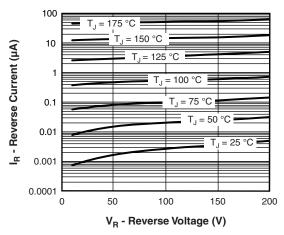


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

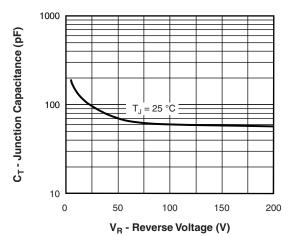


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

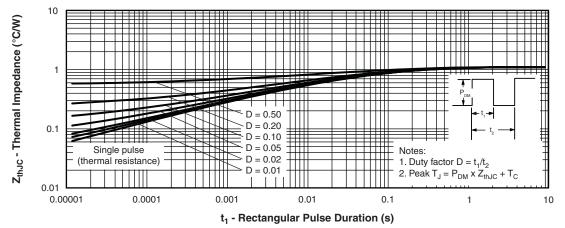


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics



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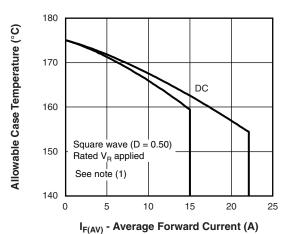


Fig. 5 - Maximum Allowable Case Temperature vs.
Average Forward Current

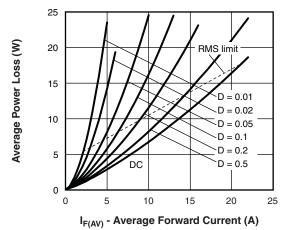


Fig. 6 - Forward Power Loss Characteristics

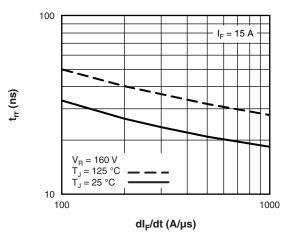


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

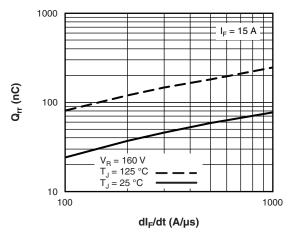
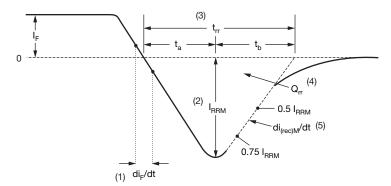


Fig. 8 - Typical Stored Charge vs. dl_F/dt

Note

 $^{(1)}$ Formula used: T_C = T_J - (Pd + Pd_{REV}) x R_{thJC}; Pd = forward power loss = I_{F(AV)} x V_{FM} at (I_{F(AV)}/D) (see fig. 6); Pd_{REV} = inverse power loss = V_{R1} x I_R (1 - D); I_R at V_{R1} = rated V_R



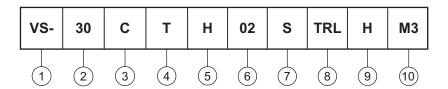
- (1) di_F/dt rate of change of current through zero crossing
 - ing and I_{RRM}
- (2) I_{RRM} peak reverse recovery current
- $Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$
- (3) t_{rr} reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.
- (5) $di_{(rec)M}/dt$ peak rate of change of current during $t_{\rm b}$ portion of $t_{\rm rr}$

(4) Q_{rr} - area under curve defined by t_{rr}

Fig. 9 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

Device code



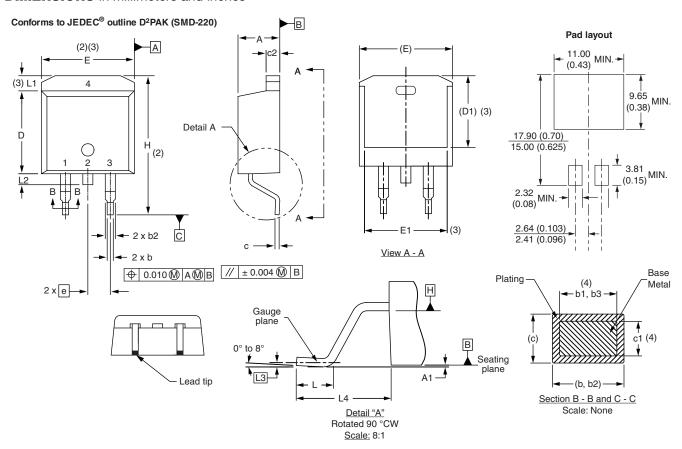
- 1 Vishay Semiconductors product
- 2 Current rating (30 A)
- C = common cathode
- 4 T = TO-220, D²PAK
- 5 H = hyperfast rectifier
- 6 Voltage rating (02 = 200 V)
- 8 • None = tube (50 pieces)
 - TRL = tape and reel (left oriented, for D2PAK package)
 - TRR = tape and reel (right oriented, for D²PAK package)
- 9 H = AEC-Q101 qualified
- 10 M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?95046				
Part marking information	www.vishay.com/doc?95444				
Packaging information	www.vishay.com/doc?95032				



D²PAK

DIMENSIONS in millimeters and inches



SYMBOL	MILLIMETERS INC		HES	NOTES	SYMBOL	MILLIM	ETERS	INC	HES	NOTES	
STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOTES	STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.06	4.83	0.160	0.190		D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010		Е	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039		E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4	е	2.54	BSC	0.100	BSC	
b2	1.14	1.78	0.045	0.070		Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4	L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029		L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4	L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065		L3	0.25	BSC	0.010	BSC	
D	8.51	9.65	0.335	0.380	2	L4	4.78	5.28	0.188	0.208	

Notes

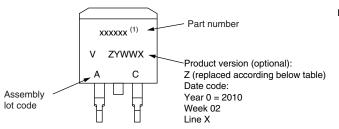
- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inch
- (7) Outline conforms to JEDEC® outline TO-263AB



Part Marking Information

Vishay Semiconductors

D²PAK



Example: This is a xxxxxx ⁽¹⁾ with assembly lot code AC, assembled on WW 02, 2010

Note

(1) If part number contain "H" as last digit, product is AEC-Q101 qualified

ENVIRONMENTAL NAMING CODE (Z)	PRODUCT DEFINITION
A	Termination lead (Pb)-free
В	Totally lead (Pb)-free
E	RoHS-compliant and termination lead (Pb)-free
F	RoHS-compliant and totally lead (Pb)-free
M	Halogen-free, RoHS-compliant, and termination lead (Pb)-free
N	Halogen-free, RoHS-compliant, and totally lead (Pb)-free
G	Green



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Vishay

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